

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A method of producing a single crystal according to Czochralski method comprising the steps of, charging polycrystalline material into a crucible, heating and melting the polycrystalline material by a heater disposed so as to surround the crucible, immersing a seed crystal into the material melt and then pulling the seed crystal to grow a single crystal, wherein in the case of growing a single crystal of which resistivity is controlled by doping with boron, the highest temperature of the crucible is controlled to be 1600°C or less to grow the single crystal.

2. (Original) The method of producing a single crystal according to Claim 1, wherein the single crystal doped with boron is grown so that the resistivity of the single crystal to be grown is 0.1 Ω cm or less.

3. (Currently Amended) The method of producing a single crystal according to ~~Claim 1 or Claim 2~~, wherein the single crystal doped with boron is grown so that the resistivity of the single crystal to be grown is 0.001 Ω cm or more.

4. (Currently Amended) The method of producing a single crystal according to ~~any one of Claims 1 – 3~~Claim 1, wherein the single crystal doped with nitrogen is grown so that concentration of nitrogen in the single crystal to be grown is from $1 \times 10^{10} /cm^3$

to 5×10^{15} /cm³.

5. (Currently Amended) The method of producing a single crystal according to ~~any one of Claims 1—4~~Claim 2, wherein a silicon single crystal is grown as the single crystal.

6. (Currently Amended) The method of producing a single crystal according to ~~any one of Claims 1—5~~Claim 3, wherein in the case of growing the single crystal, a magnetic field of at least 300 gauss or more is applied to the material melt to grow the single crystal.

7. (Currently Amended) The method of producing a single crystal according to ~~any one of Claims 1—6~~Claim 1, wherein a single crystal with a diameter of 200mm or more is grown as the single crystal.

8. (New) The method of producing a single crystal according to Claim 2, wherein a silicon single crystal is grown as the single crystal.

9. (New) The method of producing a single crystal according to Claim 3, wherein a silicon single crystal is grown as the single crystal.

10. (New) The method of producing a single crystal according to Claim 4, wherein a silicon single crystal is grown as the single crystal.

11. (New) The method of producing a single crystal according to Claim 5, wherein a silicon single crystal is grown as the single crystal.

12. (New) The method of producing a single crystal according to Claim 6, wherein a silicon single crystal is grown as the single crystal.

13. (New) The method of producing a single crystal according Claims 7, wherein in the case of growing the single crystal, a magnetic field of at least 300 gauss or more is applied to the material melt to grow the single crystal.

14. (New) The method of producing a single crystal according Claims 8, wherein in the case of growing the single crystal, a magnetic field of at least 300 gauss or more is applied to the material melt to grow the single crystal.

15. (New) The method of producing a single crystal according Claims 9, wherein in the case of growing the single crystal, a magnetic field of at least 300 gauss or more is applied to the material melt to grow the single crystal.

16. (New) The method of producing a single crystal according Claims 10, wherein in the case of growing the single crystal, a magnetic field of at least 300 gauss or more is applied to the material melt to grow the single crystal.

17. (New) The method of producing a single crystal according Claims 11, wherein in the case of growing the single crystal, a magnetic field of at least 300 gauss or more is applied to the material melt to grow the single crystal.

18. (New) The method of producing a single crystal according Claims 12, wherein in the case of growing the single crystal, a magnetic field of at least 300 gauss or more is applied to the material melt to grow the single crystal.

19. (New) The method of producing a single crystal according to Claim 17, wherein a single crystal with a diameter of 200mm or more is grown as the single crystal.

20. (New) The method of producing a single crystal according to Claim 18, wherein a single crystal with a diameter of 200mm or more is grown as the single crystal.